

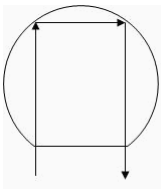
Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm
	2.0	Primary Flat Orientation	{110} +/- 1 degree
	3.0	Primary Flat Length	57.50 +/- 2.50 mm
	4.0	Secondary Flat Orientation	none
	5.0	Overall Thickness	675.00 +/- 6.00 µm
	6.0	Total Thickness Variation (TTV)	<3.00µm
	7.0	Bow	<60.00µm
	8.0	Warp	<60.00µm
	9.0	Edge Chips	0
	10.0	Edge Exclusion	5mm
HandleSilicon	11.0	Handle Growth Method	CZ
	12.0	Handle Orientation	{100} +/- 1 degree
	13.0	Handle Thickness	505.00 +/- 5.00 µm
	14.0	Handle Doping Type	P
	15.0	Handle Dopant	Boron
	16.0	Handle Resistivity	10 ~ 20 Ohmcm
	17.0	Backside Finish	Lapped/etched with lasermark
DeviceSilicon	18.0	Device Growth Method	FZ
	19.0	Device Orientation	{100} +/- 1 degree
	20.0	Oxygen Concentration	<2.5 E16 atoms/cm3
	21.0	Carbon Concentration	<3.0 E16 atoms/cm3
	22.0	Nominal Thickness	170.00 +/- 1.00 µm
	23.0	Distance to device silicon edge from wafer edge	<= 1 mm
	24.0	Device Doping Type	P
	25.0	Device Dopant	Boron
	26.0	Device Resistivity	1000 ~ 3000 Ohm-cm
	27.0	Voids	0
	28.0	Scratches	total length < 5mm
	29.0	Haze	none
	30.0	LPD Count	<35 ppw @ 0.3um

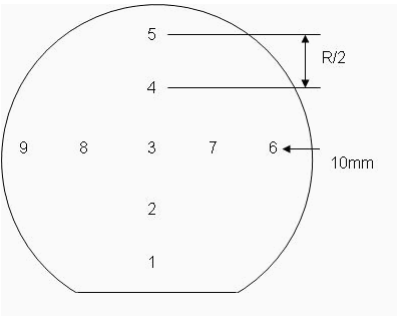
Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information